



EKM-8-8807

NMOS 128kbit MASK ROM

(16,384word × 8bit)

T-46-13-15

RP23128E

■ GENERAL DESCRIPTION

The RP23128E is static NMOS Read Only Memory organized as 16,384 words by 8-bits and operate from a single + 5V supply.

The RP23128E features automatic power-down mode. When Chip Enable (\overline{CE}) goes HIGH level, the supply current is reduced from 100mA (max.) to 20mA (max.).

These devices have Chip Enable (\overline{CE}) input and output Enable (OE/\overline{OE}) inputs allowing up to 16 wired ORs to be tied without external decoding.

According to your order, logic of the following pins may be selected.

Pin 22 (active low/active high)

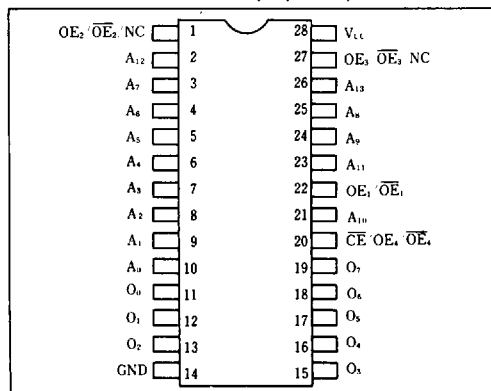
Pin 1, 27 (active low/active high/No Connection)

Pin 20 (Chip Enable/active low/active high)

■ FEATURES

- 16,384 words × 8 bits organization
- Low power dissipation: Active 550mWmax. Standby 110mW max.
- Fast access time: 200ns max.
- Single + 5V (±10%) power supply
- Completely TTL compatible: All outputs and inputs

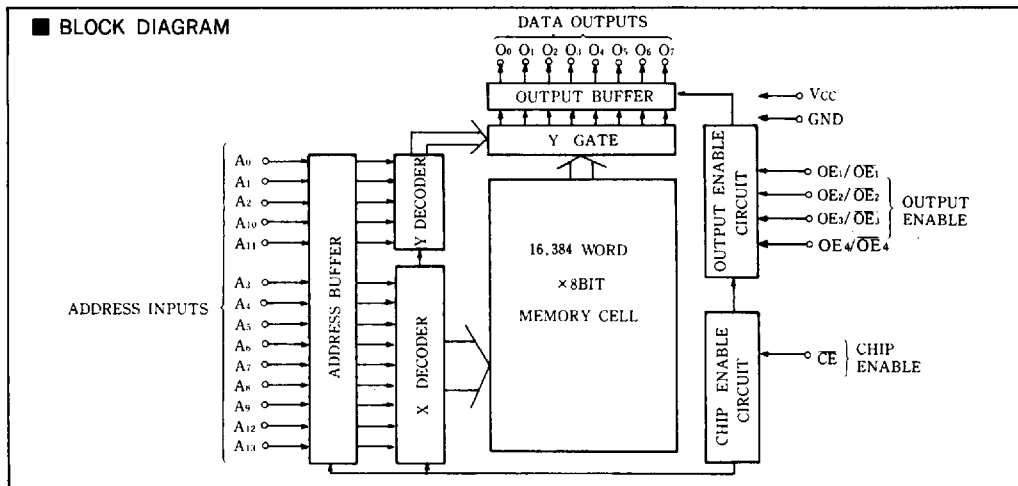
■ PIN CONFIGURATION (Top view)



■ PIN DESCRIPTION

PIN NAME	FUNCTION
A ₀ ~A ₁₃	Address Input
O ₀ ~O ₇	Data Output
$\overline{OE}_1 \sim \overline{OE}_4$	Output Enable
\overline{CE}	Chip Enable
NC	No Connection
V _{cc}	Power Supply
GND	GND

■ BLOCK DIAGRAM



RP23128E

■ ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Condition	Limit	Unit
V _{CC}	Supply Voltage	With respect to GND	-0.3~7	V
V _I	Input Voltage		-0.3~V _{CC} +0.3	V
V _O	Output Voltage		-0.3~V _{CC} +0.3	V
P _d	Maximum Power Dissipation	T _a =25°C	700	mW
T _{opr}	Operating Ambient Temperature		0~70	°C
T _{stg}	Storage Temperature		-40~125	°C

■ RECOMMENDED OPERATING CONDITIONS (T_a=0~70°C)

Symbol	Parameter	Specified Value			Unit
		Min	Typ	Max	
V _{CC}	Supply Voltage	4.5	5.0	5.5	V
V _{IH}	Input High Voltage	2.0		V _{CC}	V
V _{IL}	Input Low Voltage	-0.3		0.8	V

■ ELECTRICAL CHARACTERISTICS

● DC ELECTRICAL CHARACTERISTICS (T_a=0~70°C, V_{CC}=5V±10%)

Symbol	Parameter	Test Condition	Specified Value			Unit
			Min	Typ	Max	
I _{CC1}	Supply Current (Standby)	CE = V _{CC}			20	mA
I _{CC2}	Supply Current (Active)	I _O = 0mA			100	mA
V _{OH}	Output High Voltage	I _{OH} = -400μA	2.4			V
V _{OL}	Output Low Voltage	I _{OL} = 2.0mA			0.4	V
V _{IH}	Input High Voltage		2.0		V _{CC}	V
V _{IL}	Input Low Voltage		-0.3		0.8	V
I _{LI}	Input Leakage Current	V _I = 0V~V _{CC}	-10		10	μA
I _{LO}	Output Leakage Current	V _O = 0V~V _{CC} Chip Deselected	-10		10	μA

● AC ELECTRICAL CHARACTERISTICS (T_a=0~70°C, V_{CC}=5V±10%)

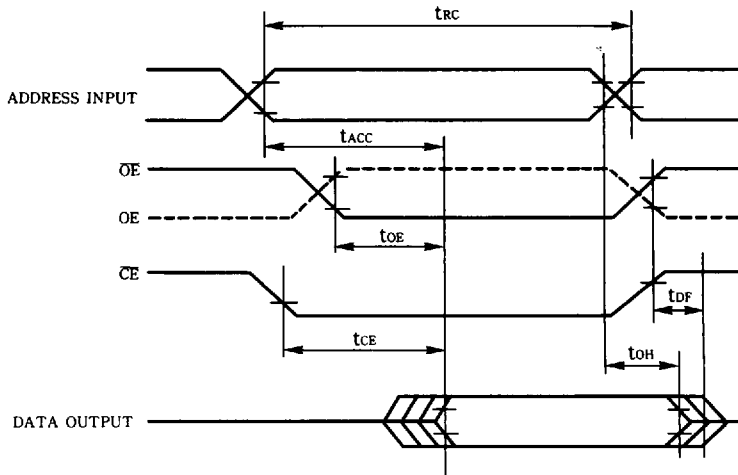
Symbol	Parameter	Specified Value			Unit
		Min	Typ	Max	
t _{RC}	Read Cycle Time	200			ns
t _{ACC}	Address Access Time			200	ns
t _{CE}	Chip Enable Access Time			200	ns
t _{OE}	Output Enable Access Time			80	ns
t _{DF}	Output Floating Delay Time			80	ns
t _{OH}	Output Hold Time	0			ns

Note) Test Condition
 Input Pulse Voltage: V_{IL}=0.6V, V_{IH}=2.4V
 Timing Measuring Voltage: Input V_{IL}=0.8V, V_{IH}=2.2V
 Output V_{OL}=0.8V, V_{OH}=2.0V
 Output Load: 1TTL + 100pF (including jig capacitance)

● TERMINAL CAPACITANCE

Symbol	Parameter	Test Condition	Specified Value			Unit
			Min	Typ	Max	
C _i	Input Capacitance	f = 1MHz			8	pF
C _o	Output Capacitance				12	pF

■ TIMING CHART



■ 28 PIN PLASTIC PACKAGE (Unit: mm)

